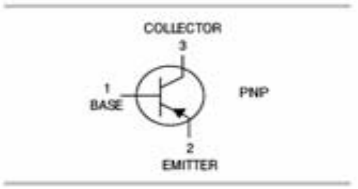
PNP Silicon Epitaxial Planar Transistor **2SB1218A**

FEATURES

- High forward current transfer ratio h_{FE}
- Excellent H_{FE} Linearity.
- Complements the 2SD1819A.

Lead-free





SOT-323

APPLICATIONS

- For general purpose amplification.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SB1218A	BQ1/BR1/BS1	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	-45	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-200	mA
P_C	Collector Dissipation	150	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	℃

PNP Silicon Epitaxial Planar Transistor **2SB1218A**

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

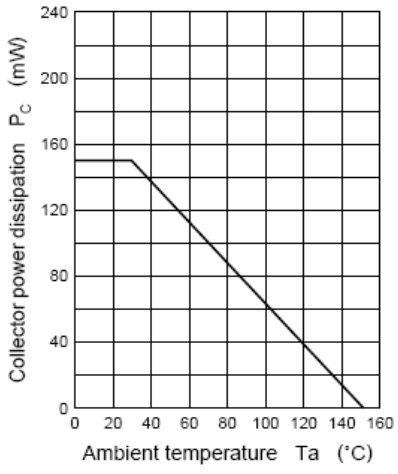
Parameter	**Symbol**	**Test conditions**	**MIN**	**TYP**	**MAX**	**UNIT**
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA,I_E=0	-45			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-2mA,I_B=0	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V,I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CB}=-10V,I_B=0			-100	μA
DC current gain	h_{FE}	V_{CE}=-10V,I_C=-2mA	160		460	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA		-0.3	-0.5	V
Transition frequency	f_T	V_{CB}=-10V, I_E=1mA f=200MHz		80		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		2.7		pF

CLASSIFICANTION OF h_{FE}

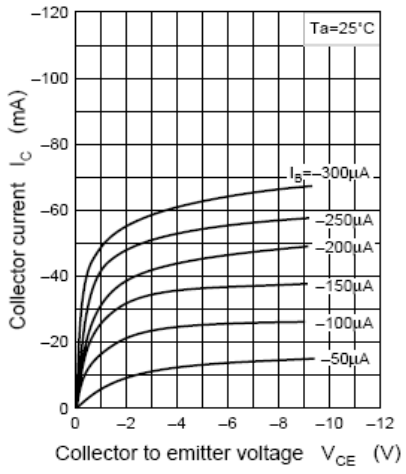
Rank	**Q**	**R**	**S**
Range	160-260	210-340	290-460
marking	BQ	BR	BS

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

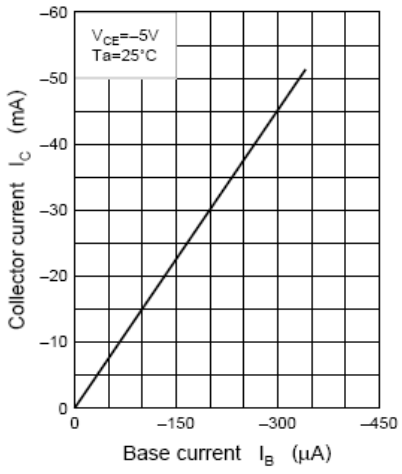
P_C — Ta



I_C — V_{CE}

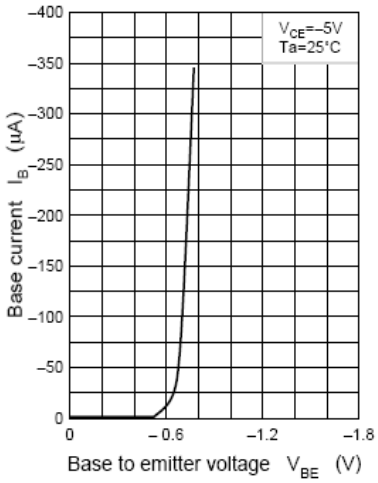


I_C — I_B

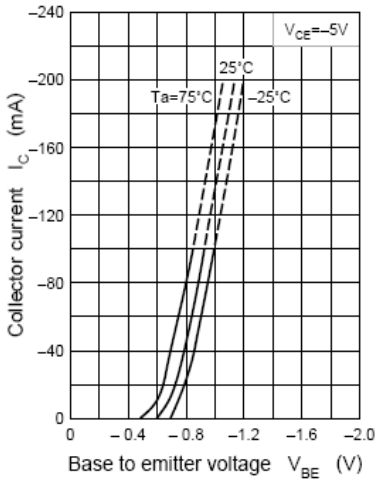


PNP Silicon Epitaxial Planar Transistor **2SB1218A**

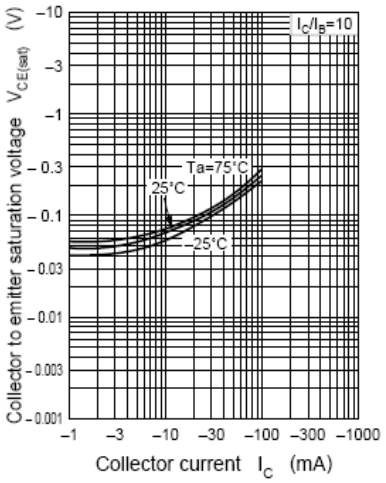
I_B — V_{BE}



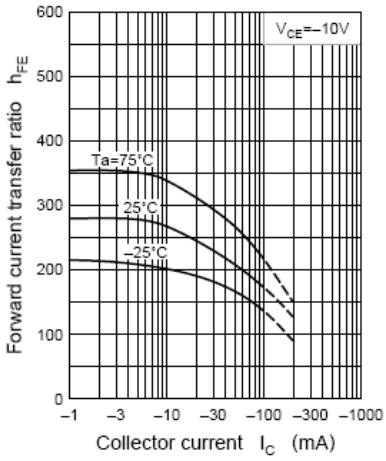
I_C — V_{BE}



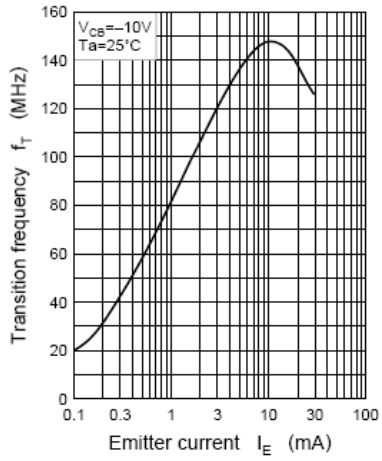
$V_{CE(sat)}$ — I_C



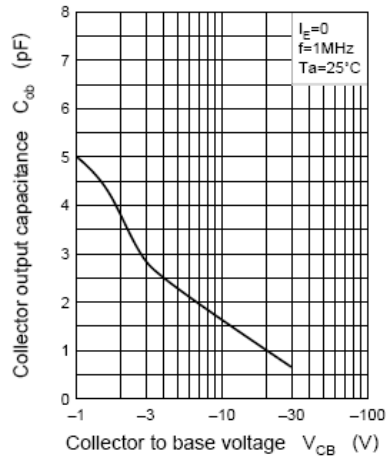
h_{FE} — I_C



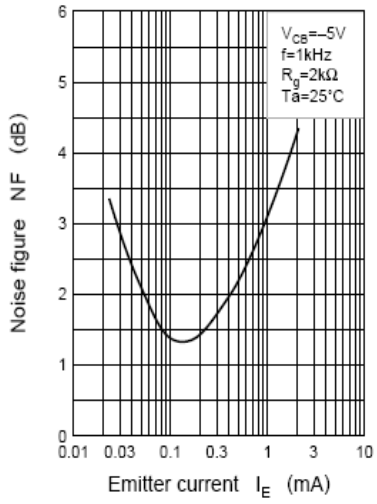
f_T — I_E



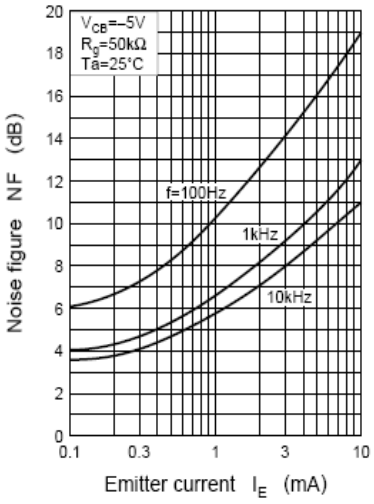
C_{ob} — V_{CB}



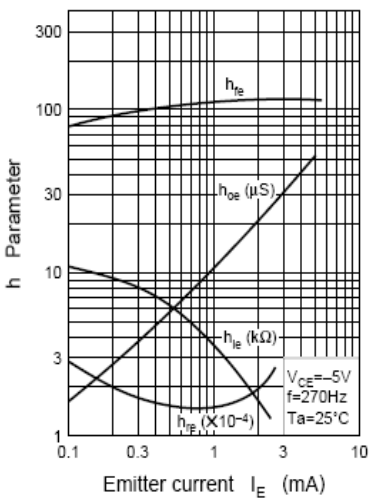
NF — I_E



NF — I_E



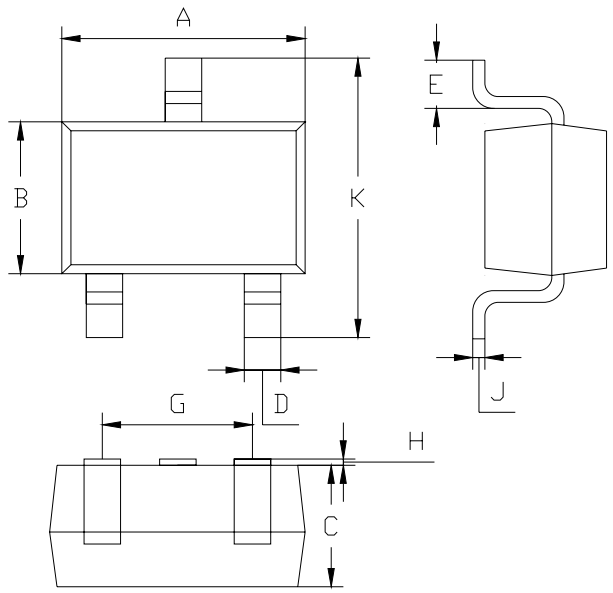
h Parameter — I_E



PNP Silicon Epitaxial Planar Transistor **2SB1218A**

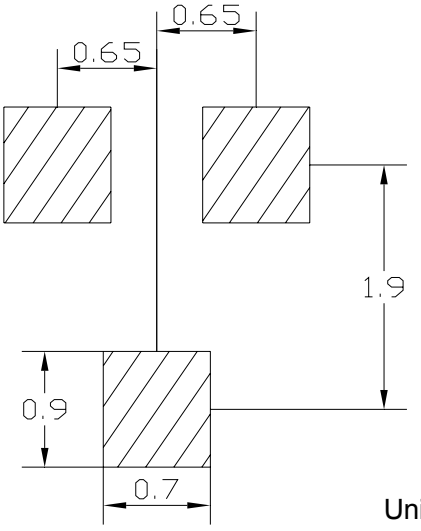
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.1	2.3
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SB1218A	SOT-323	3000/Tape&Reel